

MAR 25 2003

ATTY. DOCKET NO.

APPLICATION NO.:

4717-4600

10/069,058

LIST OF REFERENCES CITED BY APPLICANT
(Use several sheets if necessary)

APPLICANT:

Thierry Barge et al.

FILING DATE:

February 20, 2002

GROUP:

U.S. PATENT DOCUMENTS

* EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MDP	AA	5,589,422	12/1996	Bhat	437	228	
MDP	AB	5,374,564	12/1994	Bruehl	437	24	
MDP	AC	6,020,252	2/2000	Aspar et al.	438	458	
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MDP	AE	6,429,104	8/2002	Auberton-Herve	438	527	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
MDP	AF	EP 0 553 852 A	08/1993	Europe			X	
MDP	AG	EP 0 917 193 A	05/1999	Europe			X	
MDP	AH	EP 0 917 188 A	05/1999	Europe			X	
MDP	AI	FR 2 681 472 A	03/1993	France - (US equivalent 5,374,564)			X	
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MDP	AK	FR 2 774 510 A	08/1999	France - (US equivalent 6,429,104)			X	
MDP	AL	FR 2 761 526 A (US equivalent in English)	10/1998	France - (DE19753494 Abstract in English)			X	
MDP	AM	FR 2 762 136 (with English Abstract)	10/1998	France - (DE19753494 Abstract in English)			X	
MDP	AN	FR 2 761 526 (with English Abstract)	10/1998	France			X	
MDP	AO	FR 2 748 851 A (11/1997	France - (US equivalent 6,020,252)			X	
MDP	AO	DE 197 53494 English Abstract	10/1998	Germany			X	
MDP	AP	JP 10242154 (with English Abstract)	09/1998	Japan			X	

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FOREIGN PATENT DOCUMENTS (cont...)

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
<i>MDP</i>	AQ	JP 5217821 English Abstract	08/1993	Japan			X	
	AR							

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>MDP</i>	AS	Moriceau, H., et al., "Hydrogen Annealing Treatment Used to Obtain High Quality SOI Surfaces," <u>Annual IEEE International Silicon-on-insulator Conference</u> , Vol. Conf. 24, pp. 37-38, New York (1998).
<i>MDP</i>	AT	Mazara, W.P., et al., "Quality of SOI Film After Surface Smoothing With Hydrogen Annealing, Touch Polishing," <u>Proceedings of the 1997 IEEE International SOI Conference</u> , pp. 130-131, New York (1997).
<i>MDP</i>	AU	Sato, N., et al., "Hydrogen Annealed Silicon-on-insulator," <u>Applied Physics Letters</u> , Vol. 65, No. 15, pp. 1924-1926, New York (1994).

EXAMINER

DATE CONSIDERED

*Harold Sigaw-Pup**3/29/2004*

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.